

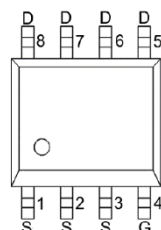
60V_{DS}/±20V N-Channel Enhancement Mode MOSFET

Features

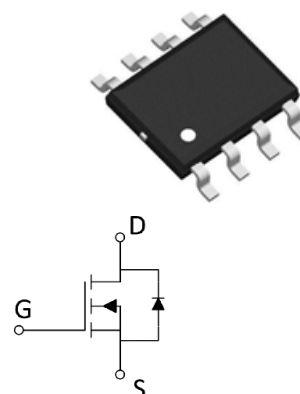
- $V_{DS}=60V, I_D=10A$
- $R_{DS(ON)}=18m\Omega$ (TYP.) $V_{GS}=10V$
- Reliable and Rugged
- Avalanche Rated
- Low On-Resistance

Applications

- Load Switch
- Power management in portable/desktop PCs
- DC/DC conversion



SOP8



Ordering Information

Device	package	Device Marking	Package Qty.
FKS6016	SOP-8	S6016	3000/PCS

Absolute Maximum Ratings ($T_C=25^{\circ}C$, unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	60	V
Gate-Source Voltage ($V_{GS}=0V$, static)	V_{GS}	±20	V
Continuous Drain Current ($T_C=25^{\circ}C$)	I_D	10	A
Continuous Drain Current ($T_C=100^{\circ}C$)		5.6	A
Pulsed Drain Current	I_{DM}	32	A
Single Pulsed Avalanche Energy	E_{AS}	69	mJ
Maximum Power Dissipation	P_D	2.1	W
Operating, Storage Temperature Range	T_J, T_{STG}	-55~150	$^{\circ}C$

Electrical Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA
Gate -Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.8	2.5	V
Drain-Source On-stage Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=1A$	-	15	19	m Ω
		$V_{GS}=4.5V, I_D=2A$	-	19	25	

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	-	-	-	$^{\circ}\text{C}/\text{W}$
Thermal Resistance,Junction-to-Ambient	$R_{\theta JA}$	-	6-	-	$^{\circ}\text{C}/\text{W}$

Dynamic Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$V_{DS}=15\text{V}$	-	1888	-	pF
Output capacitance	C_{oss}	$V_{GS}=0\text{V}$	-	112	-	
Reverse transfer capacitance	C_{rss}	$f=1\text{MHz}$	-	91	-	
Gate Resistance	R_g	$f=1\text{MHz}$	-	-	-	Ω
Total Gate Charge	Q_g	$V_{DS}=15\text{V}$	-	39	-	nC
Gate Source Charge	Q_{gs}	$V_{GS}=10\text{V}$	-	7.7	-	
Gate Drain Charge	Q_{gd}	$I_D=20\text{A}$	-	8.3	-	
Turn-on delay Time	$t_{d(on)}$	$V_{GS}=10\text{V}$	-	6.7	-	ns
Rise time	t_r	$V_{DS}=15\text{V}$	-	39	-	
Turn-off delay Time	$t_{d(off)}$	$R_L=3.5\Omega$	-	21	-	
Fall time	t_f	$R_G=6.8\Omega$	-	6.2	-	

Reverse Diode Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Body Diode Forward Voltage	V_{SD}	$V_{GS}=0\text{V}, I_{SD}=1\text{A}$	-	-	1.2	V
Reverse Recovery Time	t_{rr}	$V_{GS}=0\text{V}, I_{SD}=20\text{A}$	-	29	-	ns
Reverse Recovery Charge	Q_{rr}	$dI/dt=100\text{A}/\mu\text{s}$	-	21	-	nC

Electrical Characteristics Diagrames

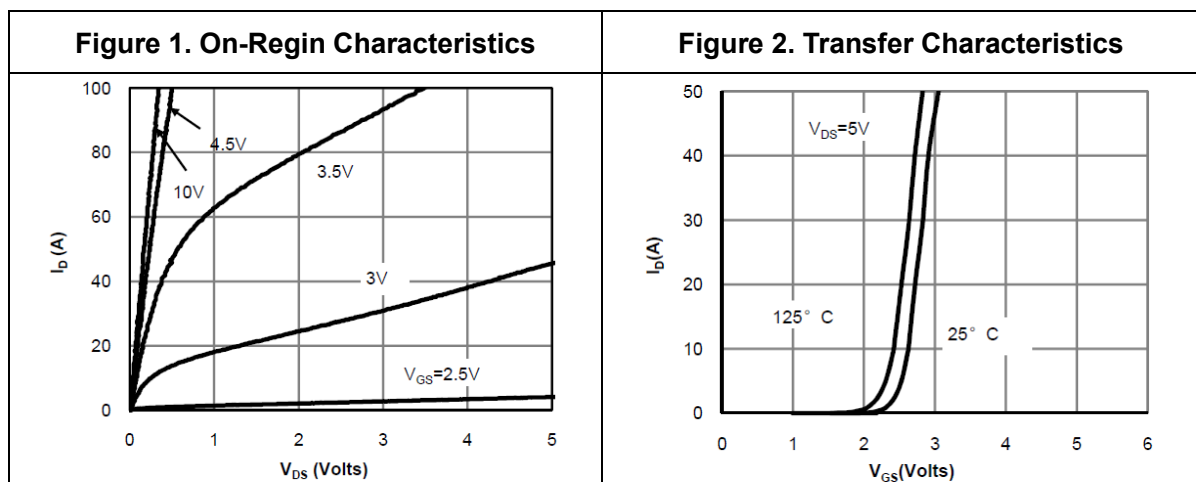


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

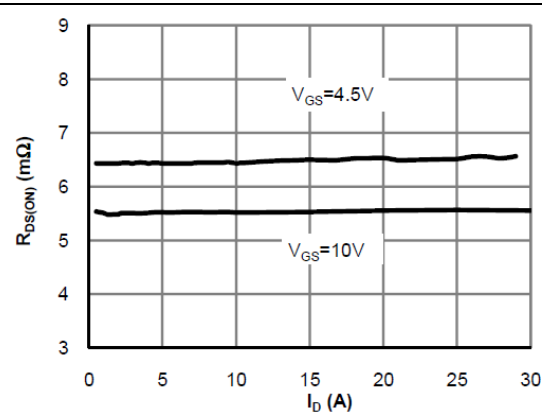


Figure 4. On-Resistance vs. Junction Temperature

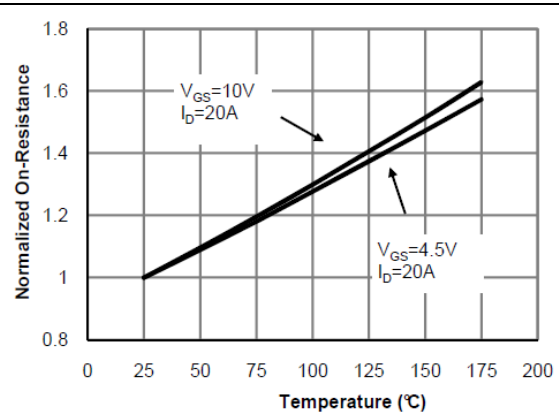


Figure 5. On-Resistance vs. Gate-Source Voltage

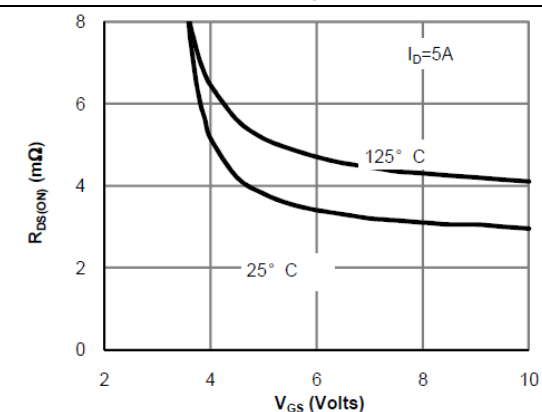


Figure 6. Body-Diode Characteristics

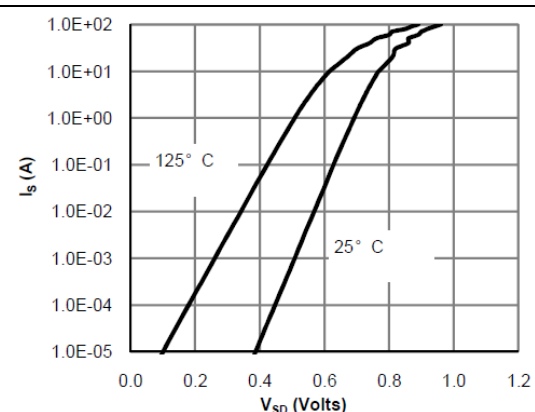


Figure 7. Gate-Charge Characteristics

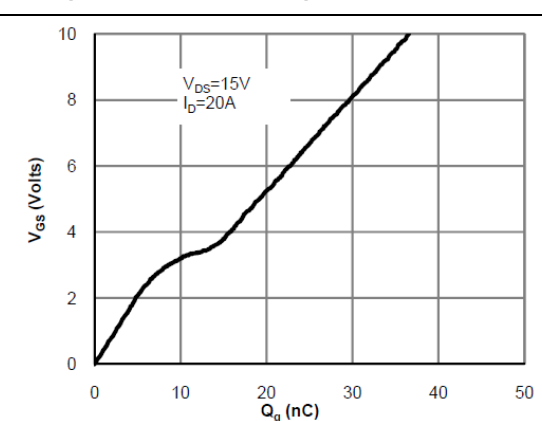


Figure 8. Capacitance Characteristics

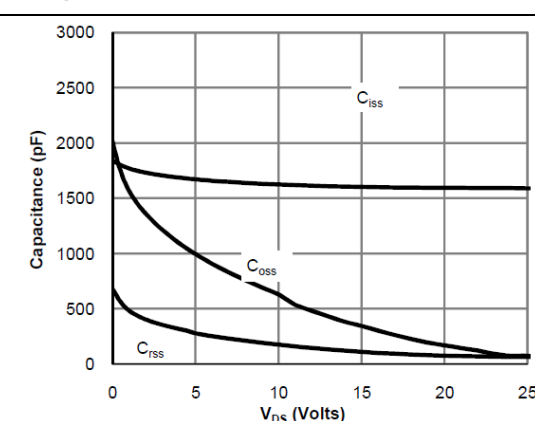


Figure 9. Maximum Forward Biased Safe Operating Area

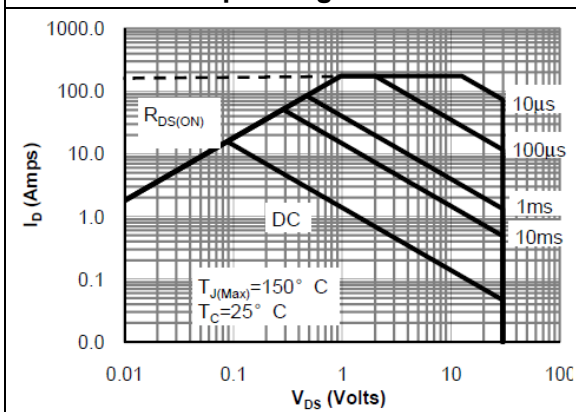


Figure 10. Single Pulse Power Rating Junction-to-Ambient

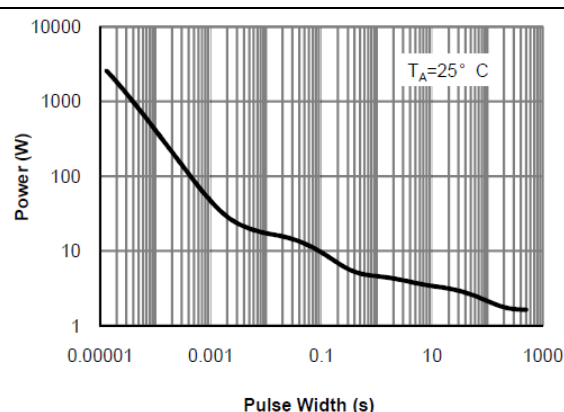
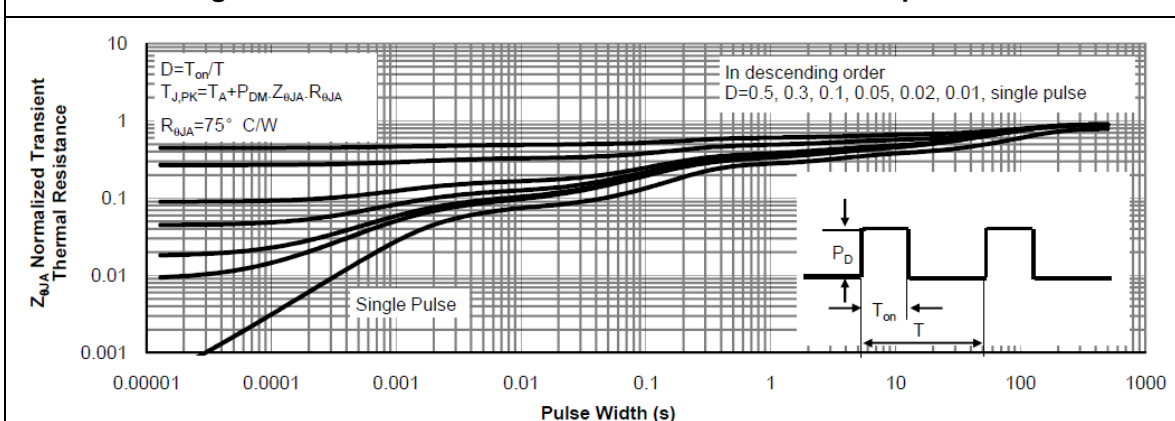


Figure 11. Normalized Maximum Transient Thermal Impedance



Physical Dimensions

SOP8

符号	尺寸 (mm)		符号	尺寸 (mm)	
	最小值	最大值		最小值	最大值
A	4.80	5.00	C3	0.05	0.20
A1	0.356	0.456	C4	0.203	0.233
A2	1.27 TYP		D	1.05 TYP	
A3	0.345 TYP		D1	0.40	0.80
B	3.80	4.00	R1	0.20 TYP	
B1	5.80	6.20	R2	0.20 TYP	
B2	5.00 TYP		θ1	17° TYP4	
C	1.30	1.60	θ2	13° TYP4	
C1	0.55	0.65	θ3	0° ~ 8°	
C2	0.55	0.65	θ4	4° ~ 12°	

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